

**J201
J202
J203**

**CASE 29-02, STYLE 5
TO-92 (TO-226AA)**

**JFET
LOW FREQUENCY/LOW NOISE**

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	40	Vdc
Drain-Gate Voltage	V _{DG}	40	Vdc
Gate-Source Voltage	V _{GS}	40	Vdc
Gate Current	I _G	50	mA
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	310 2.82	mW mW/°C
Storage Temperature Range	T _{stg}	-65 to +150	°C

Refer to 2N4220 for graphs.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage (I _G = -1.0 μA)	V _{(BR)GSS}	-40	—	Vdc
Gate Reverse Current (V _{GS} = -20 V)	I _{GSS}	—	-100	pA
Gate Source Cutoff Voltage (V _{DS} = 20 V, I _D = 10 nA)	V _{GS(off)}	-0.3 -0.8 -2.0	-1.5 -4.0 -10.0	Vdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain Current (V _{DS} = 20 V)	I _{DSS} *	0.2 0.9 4.0	1.0 4.5 20.0	mA
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance (V _{DS} = 20 V, f = 1.0 kHz)	y _{fs} *	500 1000 1500	— — —	μmhos

*Pulse Width ≤ 2.0 msec.